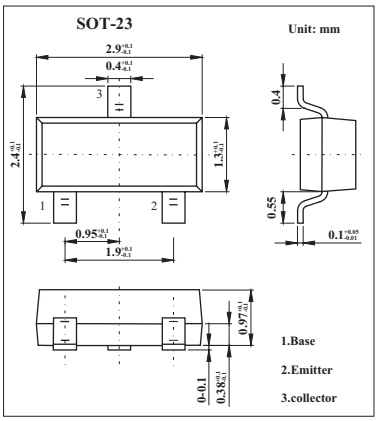
NPN Epitaxial Planar Silicon Transistor

2SC4852



Features

- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Small ON resistance.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	25	V
Collector-emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector current (pulse)	I_{CP}	200	mA
Base current	I_B	20	mA
Collector dissipation	P_C	250	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 15V, I_E=0			0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 4V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE} = 2V , I_C = 5mA	800		3200	
Gain bandwidth product	f_T	V_{CE} = 5V , I_C = 10mA		240		MHz
Output capacitance	C_{ob}	V_{CB} = 10V , f = 1.0MHz		1.4		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 10mA , I_B = 1mA		14	30	mV
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = 10mV , I_B = 1mA		0.74	1.1	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	5			V
On resistance	R_{on}	I_B = 3mA, f = 1.0MHz		0.9		Ω

Marking

Marking	YT